# MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PLED

**B16WS** 

# **Product specification**





## **FEATURES**

- Guard ring protection.
- Low forward voltage drop.
- For use in low voltage, high frequency inverters .
- High surge current capability.

#### **APPLICATIONS**

- Low voltage rectification
- Reverse polarity protection
- Low power consumption applications

#### **Reference News**

PACKAGE OUTLINE	Circuit	Marking
		SM
SOD-323		



Symbol	Parameter	Limit	Unit
VRRM	Maximum Recurrent Peak Reverse Voltage 60		V
VRMS	Maximum RMS Voltage	42	V
VDC	Maximum DC Blocking Voltage	60	V
IF	Continuous ForwardCurrent	1	А
IFSM	Non-repetitive Peak Forward Surge	10	A
IFSIM	Current@8.3mS	10	
Ptot	Total Power Dissipation	250	W
RØJA	Thermal Resistance From Junction To Ambient	400	°C/W
TJ	Operation Junction Temperature Range	-40~+ 125	°C
TSTG	Storage Temperature Range	-55~+ 150	°C
se ratings are limiting values above which the serviceability of the diode may be impaired.			

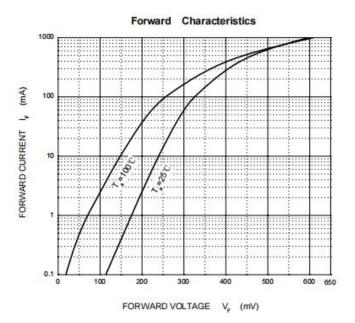
#### MAXIMUM RATING (Ta=25°C unless otherwise noted)

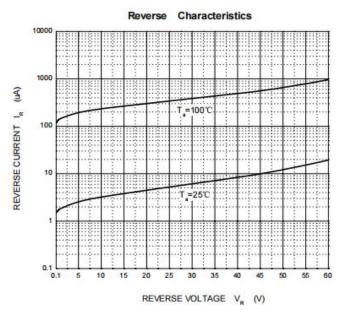
## ELECTRICAL CHARACTERISTICS (Ta=25 °C)

Symbol	Parameter	Test conditions	Min	Тур	Max	Unit
VF	Forward voltage(1)	IF=1A			0.7	V
IR	Reverse voltage leakage current	VR=60V			0.1	A
Ctot	Total Capacitance	VR=4V, f=1.0MHz			120	F

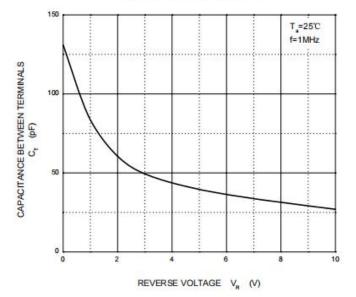
# **ELECTRICAL CHARACTERISTICS CURVE**

MICONDUCTOR

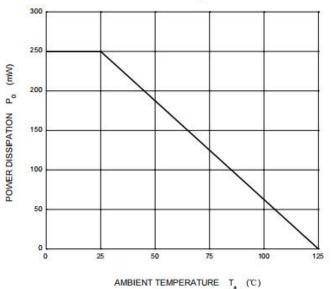




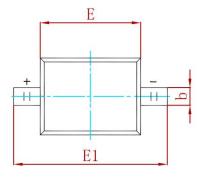
**Capacitance Characteristics** 



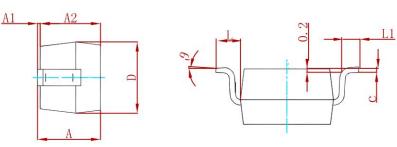
Power Derating Curve





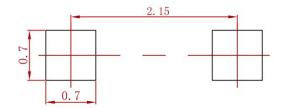


**MSKSEMI** 



Symbol	<b>Dimensions In Millimeters</b>		<b>Dimensions In Inches</b>	
Symbol	Min.	Max.	Min.	Max.
A		1.000		0.039
A1	0.000	0.100	0.000	0.004
A2	0.800	0.900	0.031	0.035
b	0.250	0.350	0.010	0.014
с	0.080	0.150	0.003	0.006
D	1.200	1 .400	0.047	0.055
E	1.600	1 .800	0.063	0.071
E1	2.550	2.750	0.100	0.108
L	0.475	REF.	0.019	REF.
е	0°	8 <sup>?</sup>	0.	8 <sup>:</sup>

# **Suggested Pad Layout**



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.

3. The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
B16WS	SOD-323	3000

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